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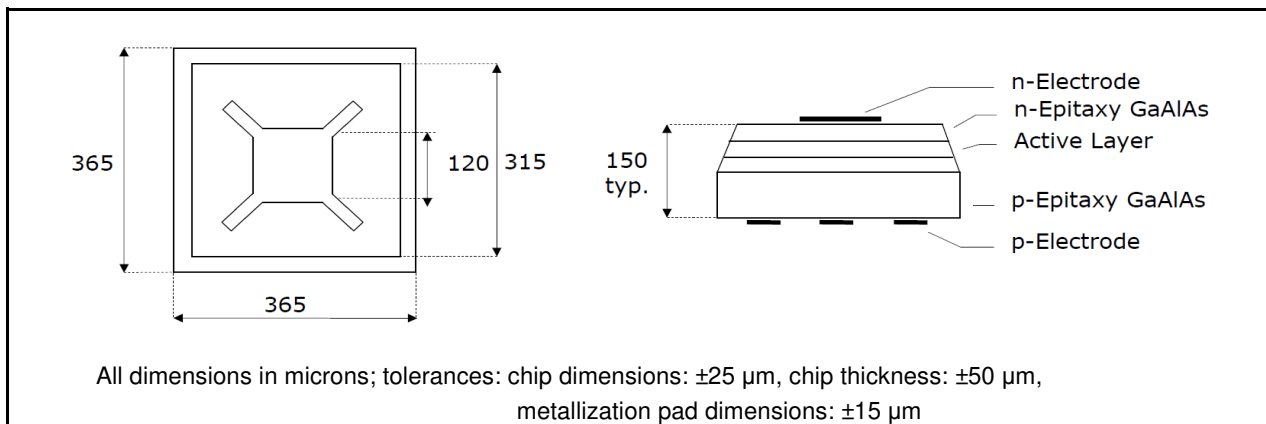
Data Sheet

LED Chip Infrared

EOLC-940-27

Rev. 01, 2016

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DHS	N (cathode) up



Mesa structure:

depth of active layer: about $20 \pm 5 \mu\text{m}$
depth of mesa: about $30 \mu\text{m}$

Electrodes:

p-side (anode): Au alloy
n-side (cathode): Au alloy

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.5	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	1.3	1.9		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	930	940	950	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		65		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		400		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No.131 151



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.